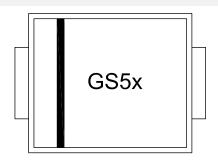


Description

- Package: DO-214AB (SMC)
- · Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- · Polarity: Color band denotes the cathode end

Making Code



Ordering information

Part Number	GS5A	GS5B	GS5D	GS5G	GS5J	GS5K	GS5M
Marking	GS5A	GS5B	GS5D	GS5G	GS5J	GS5K	GS5M
Base qty	3K						

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Rectifier Diode

Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	GS5A	GS5B	GS5D	GS5G	GS5J	GS5K	GS5M	Units
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
V _{RMS}	Maximum RMS Voltage	35	70	140	280	420	560	700	V
V _{DC}	Maximum DC Blocking Voltage	50	100	300	400	600	800	1000	V
I _{AV}	Maximum Average Forward Rectified Current		5.0						А
Forward Surge Current@60Hz		150							
I	Half-sine wave,1 cycle, T _j =25°C		150						
Forward Surge Current@1ms, quare wave, 1 cycle, T _j =25°C		300							A
V_{F}	Maximum Forward Voltage@I _{FM} =5.0A		1.1						V
I_	Maximum DC reverse current@Tj=25°C		5						uA
I _R	Maximum DC reverse current@T _j =125°C		100						
l ² t	Current squared time@1ms≤t≤8.3ms T _j =25°C		94						A^2s
C _j Typical junction capacitance Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C			22						
		33						pF	
${\sf R}_{\theta {\sf J} {\sf A}}{}^{(1)}$	Typical Thermal Resistance		48					°C/W	
TJ	Operating Junction Temperature Range		-55 to +150						°C
T _{STG}	Storage Temperature Range		-55 to +150						°C

Note: (1)Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6" x 0.6" (16 mm x 16 mm) copper pad areas

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50

0

2

Rectifier Diode

Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

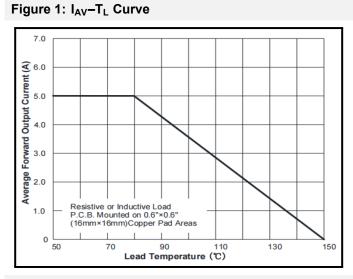
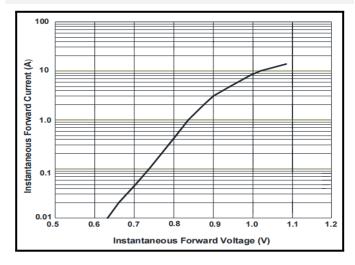


Figure 3: Typial Forward Voltage



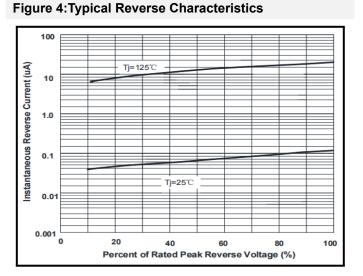
200 Peak Forward Surge Current (A) 150 8.3ms Single Half Sine Wave JEDEC Method 100

6 8 10

Number of Cycles

4

Figure 2:Surge Forward Current Capability



20

40 60 80 100

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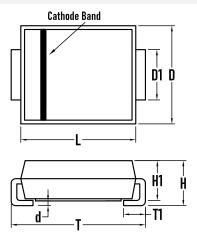
Specifications are subject to change without notice. Please refer to http://www.born-tw.com for current information. Revision: 2022-Jan-1-A

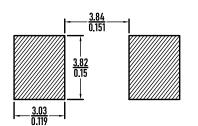




Rectifier Diode

Package Mechanical Data - SMC

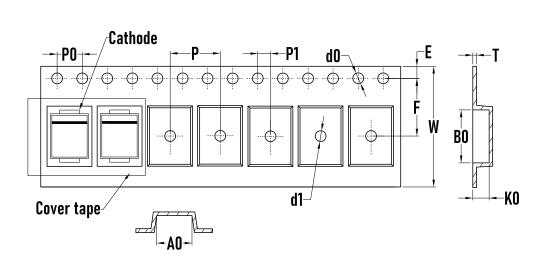




Note : dimensions : mm

SYMBOL	MILLIMETER				
STIVIDUL	MIN	MAX			
D	5.75	6.15			
D1	2.70	3.30			
Т	7.65	8.25			
T1	0.90	1.50			
d	-	0.3			
H1	2.07	2.47			
Н	2.20	2.60			
L	6.70	7.10			

Packaging Tape - SMC



SYMBOL	MILLIMETER
A0	6.00±0.1
B0	8.25±0.02
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	7.50±0.1
K0	2.70±0.1
Р	8.00±0.1
P0	4.00±0.1
P1	2.00±0.05
W	16.00±0.1
Т	0.22±0.02

MILLIMETER 323±2

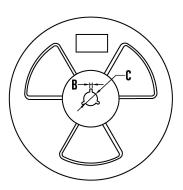
3.0±0.2

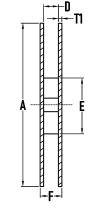
15.0±0.5

16±2 73±2

2.2±0.2 3000PCS

Packaging Reel





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SYMBOL

A B

С

D

E T1

Quantity